L Number	Hits	Search Text	DB	Time stamp
13	5041	((438/149) or (438/311) or (438/459) or	USPAT;	2004/04/18 20:21
		(438/584) or (438/706) or (438/758) or	US-PGPUB;	
		(438/795) or (438/909) or (438/935)).CCLS.	EPO; JPO;	
			DERWENT;	
		(1. 2.2) 1. 2.2(-1.)	IBM_TDB	2004/04/18 20:22
14	37845	(hold or holding) near portion	USPAT; US-PGPUB;	2004/04/18 20.22
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
15	20782	SOI or (silicon adj on adj insulator)	USPAT;	2004/04/18 20:23
13	20702	SOI OI (SIIICON da) ON da) INDAIdeoi,	US-PGPUB;	,
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
16	23846	reducing near atmosphere	USPAT;	2004/04/18 20:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	805976	hydrogen	USPAT;	2004/04/18 20:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(/1 -1 d b -1 dimm) many montion) game (COI	IBM_TDB USPAT;	2004/04/18 20:24
18	2	((hold or holding) near portion) same (SOI or (silicon adj on adj insulator))	US-PGPUB;	2004/04/18 20.24
		or (Stricon adj on adj insuracor)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
19	96	((hold or holding) near portion) and (SOI or	USPAT;	2004/04/18 20:24
		(silicon adj on adj insulator))	US-PGPUB;	
		·	EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
20	1	1 ' ' '	USPAT;	2004/04/18 20:24
		or (silicon adj on adj insulator))) and	US-PGPUB;	
		(reducing near atmosphere)	EPO; JPO; DERWENT;	
			IBM TDB	
21	1	((((hold or holding) near portion) and (SOI	USPAT;	2004/04/18 20:24
21	_	or (silicon adj on adj insulator))) and	US-PGPUB;	
		(reducing near atmosphere)) and hydrogen	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	34	silicon adj boat	USPAT;	2002/11/20 18:41
			US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
-]	giligen adi beat	IBM_TDB USPAT;	2002/11/20 11:08
	34	silicon adj boat	US-PGPUB;	2002/11/20 11:00
			EPO; JPO;	
			DERWENT;	*
			IBM TDB	
-	60174	silicon adj carbide	USPAT;	2002/11/20 18:18
			US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/11/00 10 10
-	92082	cvd	USPAT;	2002/11/20 18:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	2120	(silicon adj carbide) same cvd	USPAT;	2002/11/20 18:18
	2120	(SIIICON da) Calbiac, Same Cva	US-PGPUB;	-302, 22, 20 10.10
			EPO; JPO;	
	1		DERWENT;	
l .			1	

G6246 boat	18:18 19:44 18:43
The content of the	19:44 18:43
DERMENT; IBM_TDB USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWE	19:44 18:43
Comparison of the content of the c	19:44 18:43
1	19:44 18:43
Sepon	19:44 18:43
EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO;	18:43 18:43
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	18:43 18:43
34 silicon adj boat USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPA	18:43 18:43
Silicon adj carbide Same cvd Same boat US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPAT; US-PGPUB; EPO; JPO; D	18:43 18:43
1	18:43
1	18:43
1	18:43
- 1 (((silicon adj carbide) same cvd) same boat) and (silicon adj boat) - 74 (((silicon adj carbide) same cvd) same boat) or (silicon adj boat) - 14400 soi - 14400 soi - 34 silicon adj boat - 34 silicon adj boat - 35 silicon adj boat - 36 silicon adj boat - 37 soi same (silicon adj boat) - 38 soi same (silicon adj boat) - 39 soi same (silicon adj boat) - 3002/11/20 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB;	18:43
and (silicon adj boat) 1	18:43
EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; ISM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	
TBM_TDB	
or (silicon adj boat) or (silicon adj boat) 14400 soi 14400 soi 1500 soi 1600 soi 1700 soi 1800 soi	
or (silicon adj boat) 14400 soi 1500 soi 1600 soi 1700 soi 1800 s	19:43
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	19:43
TBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	19:43
- 14400 soi USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	19:43
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	19:43
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	
- 34 silicon adj boat USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	
- 34 silicon adj boat USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; DERWENT;	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	19:44
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	
IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	
Soi same (silicon adj boat) USPĀT; US-PGPUB; EPO; JPO; DERWENT;	
US-PGPUB; EPO; JPO; DERWENT;	10 45
EPO; JPO; DERWENT;	19:46
DERWENT;	
IBM TDB	
- 1146922 semiconductor USPAT; 2002/11/21	19:50
US-PGPUB;	
EPO; JPO;	
DERWENT;	
IBM_TDB	
5 (silicon adj boat) same semiconductor USPAT; 2002/11/21	19:46
US-PGPUB;	
EPO; JPO;	
DERWENT; IBM_TDB	
- 12 semiconductor adj on adj insulat\$3 USPAT; 2003/11/07	18:28
US-PGPUB;	, .
EPO; JPO;	
DERWENT;	
IBM_TDB	
- 14562 soi USPAT; 2002/12/02	11:04
US-PGPUB;	
EPO; JPO;	
DERWENT;	
	11:04
- 508529 transistor USPAT; 2002/12/02 US-PGPUB;	
EPO; JPO;	
DERWENT;	
IBM_TDB	
_ 3801 soi same transistor USPAT; 2002/12/02	
US-PGPUB;	11:04
EPO; JPO;	11:04
DERWENT;	11:04
IBM_TDB	11:04

	60532	silicon adj carbide	USPAT;	2002/12/02 11:04
	00332		US-PGPUB; EPO; JPO;	
	1		DERWENT;	
		(soi same transistor) same (silicon adj	<pre>IBM_TDB USPAT;</pre>	2003/11/07 18:28
-	10	carbide)	US-PGPUB;	2000, 22, 27
		04222407	EPO; JPO;	
			DERWENT; IBM TDB	
_	15468	soi or (silicon near2 insulator)	USPAT;	2003/05/18 20:25
			US-PGPUB USPAT;	2003/05/18 20:25
-	265	silicon near2 boat	US-PGPUB	2003/03/10 20:23
_	14	(soi or (silicon near2 insulator)) and	USPAT;	2003/05/18 20:26
	13	(silicon near2 boat) ((soi or (silicon near2 insulator)) and	US-PGPUB USPAT;	2003/05/18 20:27
-	13	(silicon near2 boat)) and @ad<20020307	US-PGPUB	
-	1	("6468884").PN.	USPAT; US-PGPUB	2003/10/29 10:53
	4619	((438/149) or (438/311) or (438/459) or	USPAT;	2004/04/18 20:21
	1017	(438/584) or (438/706) or (438/758) or	US-PGPUB;	
		(438/795) or (438/909) or (438/935)).CCLS.	EPO; JPO; DERWENT;	
			IBM_TDB	
-	405	(silicon or ((single near2 crystal) adj	USPAT;	2003/11/07 14:33
	ļ	silicon) or (poly near2 silicon) or (silicon near2 carbide)) near2 boat	US-PGPUB; EPO; JPO;	
		near cars as, , near see	DERWENT;	
		(((438/149) or (438/311) or (438/459) or	IBM_TDB USPAT;	2003/11/07 14:26
_	20	(438/584) or (438/706) or (438/758) or	US-PGPUB;	2003, 22, 01 20121
		(438/795) or (438/909) or (438/935)).CCLS.)	EPO; JPO;	
		and ((silicon or ((single near2 crystal) adj silicon) or (poly near2 silicon) or (silicon	DERWENT; IBM TDB	
		near2 carbide)) near2 boat)	_	
-	100	(silicon near2 carbide) near2 boat	USPAT; US-PGPUB;	2003/11/07 18:29
			EPO; JPO;	
			DERWENT; IBM TDB	
_	8	(((438/149) or (438/311) or (438/459) or	USPAT;	2003/11/07 14:33
		(438/584) or (438/706) or (438/758) or	US-PGPUB; EPO; JPO;	
		(438/795) or (438/909) or (438/935)).CCLS.) and ((silicon near2 carbide) near2 boat)	DERWENT;	
			IBM_TDB	0000/11/07 1: 5=
-	0 5	1	USPAT USPAT	2003/11/07 14:37 2003/11/07 14:37
_	5	"5029554" "6139642").PN.		
-	7513	The state of the s	USPAT; US-PGPUB;	2003/11/07 18:29
		near2 substrate	EPO; JPO;	
			DERWENT;	
_	100	(silicon near2 carbide) near2 boat	IBM_TDB USPAT;	2003/11/07 18:30
	100	(SIIICON NEWLE CALELAGY NOWLE SOME	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	2	((soi or(semiconductor adj on adj	USPAT;	2003/11/07 18:30
		insulat\$3)) near2 substrate) same ((silicon near2 carbide) near2 boat)	US-PGPUB; EPO; JPO;	
		The state of the s	DERWENT;	
			IBM_TDB	<u></u>